



40V +175°C P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	RDS(ON) Max	I _D Tc = +25°C
-40V	13mΩ @ V _{GS} = -10V	-69A
-40 V	$23m\Omega$ @ V _{GS} = -4.5V	-52A

Features and Benefits

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Description and Applications

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

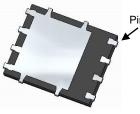
- Reverse Polarity Protection
- BLDC Motor Control
- Power Management Functions

Mechanical Data

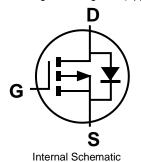
- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish 100% Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208³
- · Weight: 0.097 grams (Approximate)

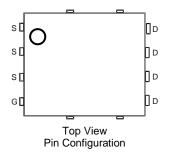






Bottom View





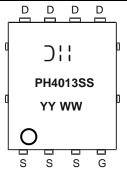
Ordering Information (Note 4)

Part Number	Case	Packaging
DMPH4013SPS-13	PowerDI5060-8	2,500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- $4. For packaging details, go to our website at \ https://www.diodes.com/design/support/packaging/diodes-packaging/.\\$

Marking Information



) | | = Manufacturer's Marking PH4013SS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 20 = 2020) WW = Week (01 to 53)

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DMPH4013SPS

Document number: DS42173 Rev. 2 - 2

1 of 7



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	-40	V		
Gate-Source Voltage	V_{GSS}	±20	V		
Continuous Drain Current $V_{GS} = -10V$ (Note 7) Steady $T_{C} = +25^{\circ}C$ State $T_{C} = +100^{\circ}C$			lo	-69 -49	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	-277	А		
Maximum Body Diode Continuous Current (Note 7)			Is	-69	Α
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)			Ism	-277	А
Avalanche Current (Note 8) L = 1mH			las	-22	Α
Avalanche Energy (Note 8) L = 1mH			Eas	260	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	98	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	PD	3.3	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	45	°C/W
Thermal Resistance, Junction to Case (Note 7)		Rejc	1.6	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

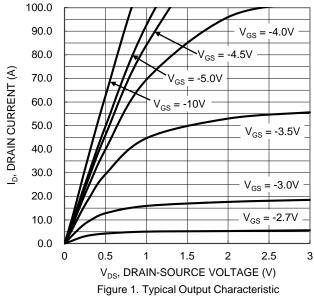
Characteristic	Symbol	Min	Tun	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)	Symbol	IVIIII	Тур	IVIAX	Unit	rest Condition
, ,	D)/	-40		1	V	\/ 0\/ I- 050··A
Drain-Source Breakdown Voltage	BVDSS					VGS = 0V, ID = -250µA
Zero Gate Voltage Drain Current	I _{DSS}	_		-1	μΑ	$V_{DS} = -40V, V_{GS} = 0V$
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	VGS(TH)	-1	-1.8	-3	V	$V_{DS} = V_{GS}$, $I_{D} = -250\mu A$
Static Drain-Source On-Resistance	Process	_	9	13	mΩ	$V_{GS} = -10V, I_{D} = -10A$
Static Diam-Source On-Intesistance	RDS(ON)	_	12.4	23	1112.2	$V_{GS} = -4.5V, I_{D} = -8A$
Diode Forward Voltage	VsD	_	-0.70	-1.2	V	V _G S = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	Ciss	_	4763	_		V _{DS} = -20V, V _{GS} = 0V f = 1MHz
Output Capacitance	Coss	_	539	_	pF	
Reverse Transfer Capacitance	C _{rss}	_	403	_		
Gate Resistance	Rg	_	7.4		Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	39			V _{DS} = -20V, I _D = -10A
Total Gate Charge (V _{GS} = -10V)	Qg	_	87	_	nC	
Gate-Source Charge	Qgs	_	12.5		IIC	
Gate-Drain Charge	Q_{gd}	_	15	_		
Turn-On Delay Time	td(ON)	_	6.2	_		$V_{GS} = -10V, V_{DD} = -20V,$ $R_{G} = 3\Omega, I_{D} = -10A$
Turn-On Rise Time	t _R	_	4.8	_		
Turn-Off Delay Time	tD(OFF)	_	126	_	ns	
Turn-Off Fall Time	t _F	_	57	_		
Reverse Recovery Time	t _{RR}		27	_	ns	I _F = -10A, di/dt = -100A/μs
Reverse Recovery Charge	Qrr	_	21	_	nC	I _F = -10A, di/dt = -100A/μs

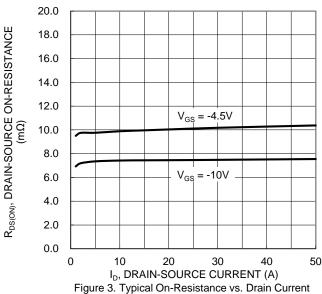
Notes:

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 9. Short duration pulse test used to minimize self-heating effect.
 10. Guaranteed by design. Not subject to product testing.

2 of 7 DMPH4013SPS January 2020 © Diodes Incorporated Document number: DS42173 Rev. 2 - 2







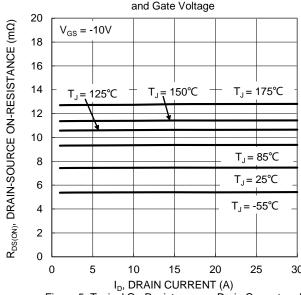


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

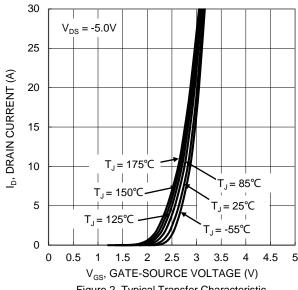
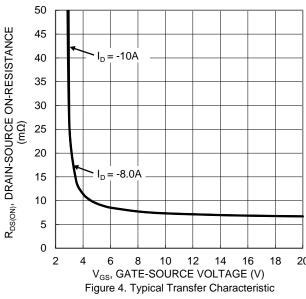


Figure 2. Typical Transfer Characteristic



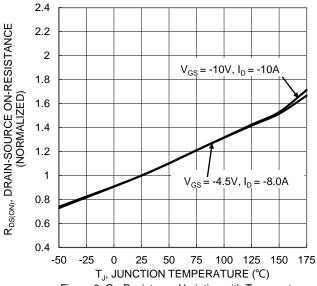


Figure 6. On-Resistance Variation with Temperature



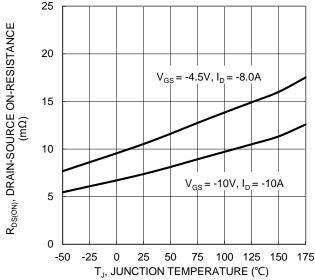
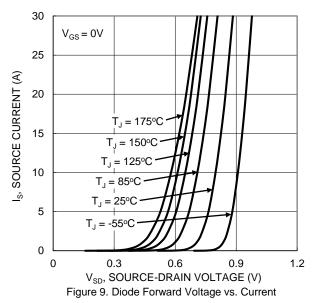
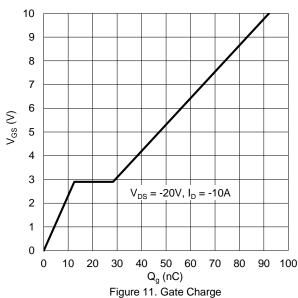


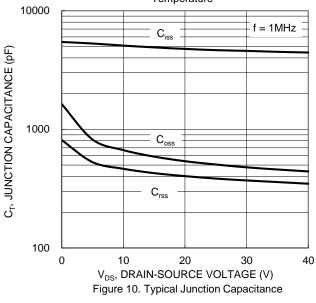
Figure 7. On-Resistance Variation with Temperature

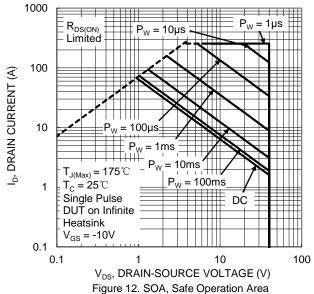




3 V_{GS(TH)}, GATE THRESHOLD VOLTAGE (V) 2.5 $I_D = -1mA$ 2 1.5 $I_{D} = -250 \mu A$ 1 0.5 0 -50 -25 0 25 50 75 100 125 150 175 T_J, JUNCTION TEMPERATURE (°C)

Figure 8. Gate Threshold Variation vs. Junction Temperature







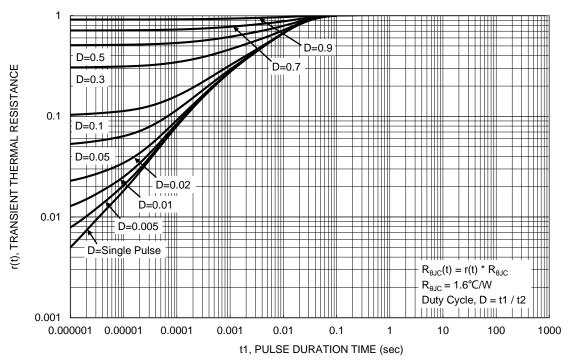


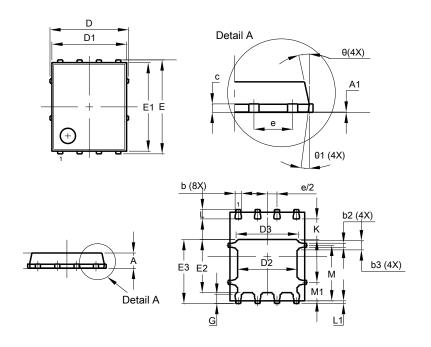
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

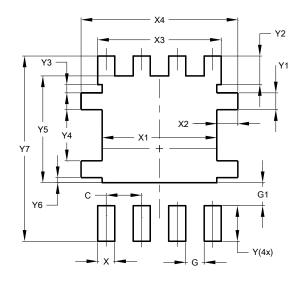


PowerDI5060-8					
Dim	Min	Typ 1.00			
Α	0.90	0.90 1.10			
A1	0.00	0.05	_		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D	ţ	5.15 BSC			
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Е		6.15 BSC	•		
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	3.99 4.39 4.			
е	,	1.27 BSC			
G	0.51	0.71	0.61		
K	0.51	_	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
М	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
Х3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

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7 of 7 DMPH4013SPS Document number: DS42173 Rev. 2 - 2

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